

LED CHIP LED C630-35V

SPECIFICATION OF LED CHIP
C630-35V
[Red]

1) Commodity Type and Physical Characteristics.

- | | | |
|----------------------|-------------------------------|----------------|
| 1. Material | InGaAlP/GaAs | |
| 2. Electrode | Top Side P (anode)side | :Au Alloy/ Pad |
| | Bottom Side N (cathode)side | :Au Alloy |
| 3. Electrode Pattern | | Fig.1 |
| 4. Chip Size | | Fig.2 |
| 5. Chip Thickness | | Fig.2 |
| 6. Emission Area | | Fig.2 |

2) Electro-Optical Characteristics [Ta=25°C]

Parameters	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf	If=20mA		1.9	2.4	V
Reverse Current	Ir	Vr=5V			10	uA
Brightness	Iv	If=20mA	40	90		mcd
Power Intensity	Po	If=20mA	0.7	1.2		mW
Peak Wavelength	I P	If=20mA	620	630	640	nm
Spectral Radiation Bandwidth	DI	If=20mA		20		nm
RiseTime	tr	If=20mA		100		ns
FallTime	tf	If=20mA		100		ns

‡ Die shall be mounted on TO=18 gold header without resin coated.

[Unit: um]

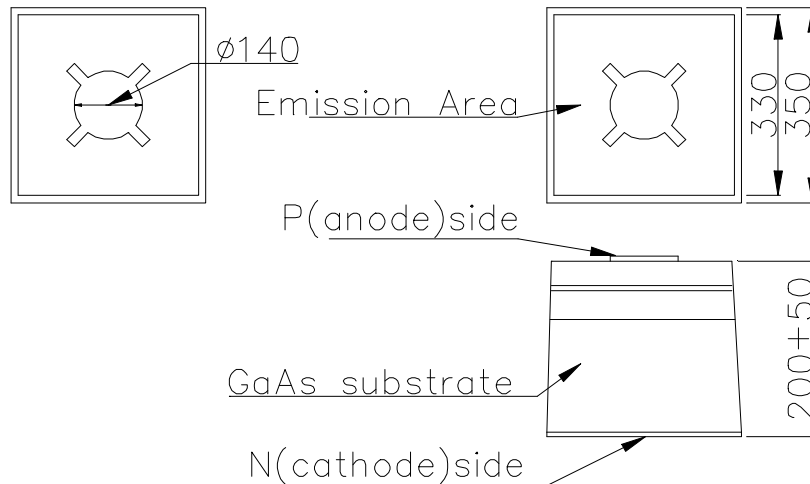


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area